Features in This Issue

Simulation of the Charge Collection in a Nonuniform Electric Field for MAPbI$_3$ Semiconductor Nuclear Detector With Schottky Contact

by XHua Meng, Juan Qin, Yongsheng Yi, Run Xu, Gang Cao, Wenzhen Wang, Huanzhen Qi, Dongmei Li, Haitao Xu, Jianming Lai, Fei Xu, Feng Hong, and Linjun Wang

Investigation on the Fast Component Light Yield of BaF$_2$:Y Crystal

by Chen Peng, Kan Zhang, Lei Yang, Jiaqian Zheng, Yi Lu, Yueyun Hou, Xinlong Yan, Zhaoji Shi, Hetong Han, Zhaohui Song, Junfeng Chen, and Fan Yang

Accurate FIT Rate Estimation Through High-Level Software Fault Injection

by Pablo R. Bodmann, Daniel Oliveira, and Paolo Rech

NIEL Calculations for III–V Compound Semiconductors Under Electron or Proton Irradiation

by A. Akkerman, J. Barak, and M. Murat